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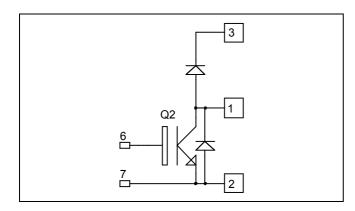




Boost chopper Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 600V$$

 $I_{C} = 300A$ @ $Tc = 80^{\circ}C$



Application

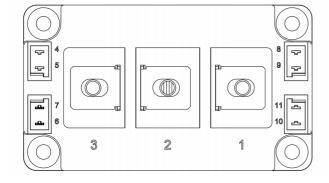
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



All ratings @ $T_i = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25$ °C	400	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	300	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	940	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	600A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				500	μΑ
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V CE(sat)	Confector Emitter Saturation Voltage	$I_C = 300A$ $T_j = 150$ °C	$T_{j} = 150^{\circ}C$		1.7		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 4.8 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		18.5		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		1.2		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.5		
Q_{G}	Gate charge	V_{GE} =±15V, I_{C} =300A V_{CE} =300V		3.2		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (2:	5°C)	110		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 300A$		490		ns
T_{f}	Fall Time	$R_G = 2.2\Omega$		50		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (1:	50°C)	130		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		60		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300V$ $I_{\text{C}} = 300A$		530		
T_{f}	Fall Time	$R_G = 2.2\Omega$		70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_{i} = 2$	25°C	3.1		
Lon	Turn on Energy		150°C	3.3		mJ
E_{off}	Turn off Energy	$I_C = 300A$ $T_i = 2$		12		1113
-off	Turn on Energy	$R_G = 2.2\Omega$ $T_j = 1$	150°C	12.5		
I_{sc}	Short Circuit data	$V_{GE} \le 15V$; $V_{Bus} = 360$ ° $t_p \le 6\mu s$; $T_i = 150$ °C	V	1500		A

Reverse diode ratings and characteristics

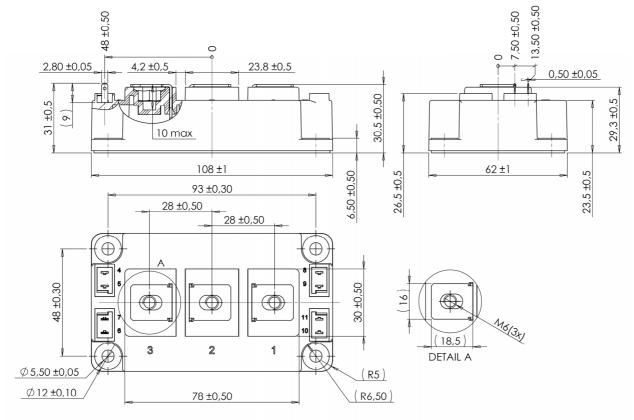
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RRM}	Maximum Reverse Leakage Current	$V_R=600V$	$T_{\rm j} = 25^{\circ}{\rm C}$ $T_{\rm i} = 150^{\circ}{\rm C}$			500 750	μΑ
I_{F}	DC Forward Current		$T_i = 130 \text{ C}$ $T_c = 80^{\circ}\text{C}$		300	/30	A
V	V_F Diode Forward Voltage $I_F = 300A$ $V_{GE} = 0V$	$I_F = 300A$	$T_i = 25^{\circ}C$		1.6	2	V
V _F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		
_	Danier Danier Time		$T_i = 25^{\circ}C$		100		
ι_{rr}	t _{rr} Reverse Recovery Time	$T_{i} = 150^{\circ}C$		150		ns	
	Daniera Daniera Chara	$I_F = 300A$ $V_R = 300V$ $di/dt = 4800A/\mu s$	$T_i = 25^{\circ}C$		14.4		μС
Q_{rr}	Reverse Recovery Charge		$T_i = 150^{\circ}C$		30.4		
Г	D D E	αι/αι 1000/1/μ3	$T_i = 25^{\circ}C$		3.4		т
E_{rr}	Reverse Recovery Energy		$T_{\rm j} = 150^{\circ}{\rm C}$		7.2		mJ



Thermal and package characteristics

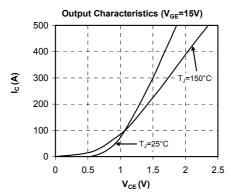
Symbol	Characteristic			Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.16	°C/W	
IX _{th} JC			Diode			0.25	C/ W	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V	
T_{J}	Operating junction temperature range			-40		175		
T_{STG}	Storage Temperature Range	-40	125 °C					
$T_{\rm C}$	Operating Case Temperature			-40		125		
Torque	Mounting torque	For terminals	M6	3		5	N.m	
		To Heatsink	M6	3		5	18.111	
Wt	Package Weight					350	g	

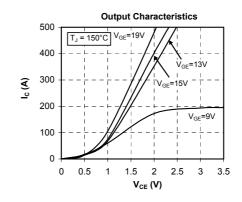
D3 Package outline (dimensions in mm)

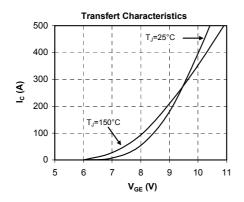


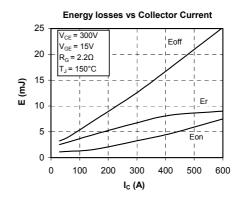


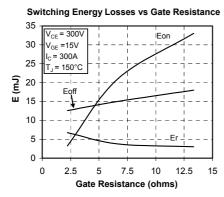
Typical Performance Curve

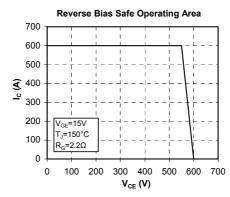


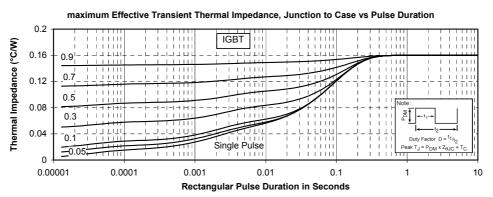






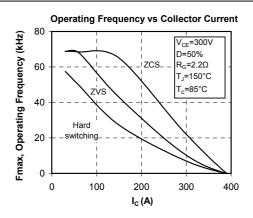


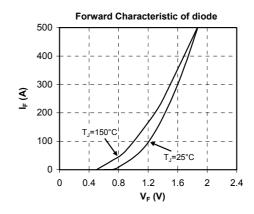


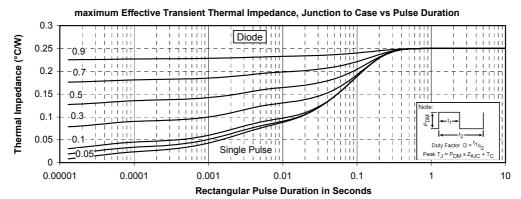


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